

Search History. (16 pp incl parent) 5/3/5

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	("5414282").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 07:49
L2	1	1 and pnp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 08:31
L3	0	pnp near3 optoelectronic adj switch and bipolar	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 08:31
L4	0	pnp near3 optoelectronic adj switch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 08:32
L5	6356	pnp and bipolar adj transistor and (light-emitting adj diode device)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 08:33
L6	786	pnp and bipolar adj transistor.ti, ab,clm. and (light-emitting adj diode device).ti,ab,clm. and switch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 08:33
L7	3	pnp and bipolar adj transistor.ti, ab,clm. and (light-emitting adj diode device).ti,ab,clm. and optoelectronic adj switch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 09:34
L8	5	((("5,476,811") or ("6,350,997") or ("5,159,603") or ("6,072,189") or ("5,010,382")).PN.	US-PGPUB; USPAT	OR	OFF	2005/05/04 09:35
L9	2	jp-60167390\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 09:55
L10	2	jp-61231788\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 09:36

L11	2	jp-61270885\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 09:38
L12	2	jp-62189750\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 09:39
L13	2	jp-62244186\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 09:39
L14	2	jp-63024692\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 09:40
L15	2	jp-61059793\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 09:41
L16	2	jp-04075347\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 09:41
L17	2	jp-02280338\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 09:42
L18	2	jp-03008340\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 09:42
L19	2	jp-61053768\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 09:43
L20	2	jp-61131491\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 09:43

L21	24	9 10 11 12 13 14 15 16 17 18 19 20	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 09:56
L22	5	8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 09:57
L23	12974	((257/79) or (257/8\$1) or (257/9\$1) or (257/100) or (257/101) or (257/102) or (257/103) or (372/4\$1) or (372/50) or (257/565)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/05/04 10:02
L24	47	23 and graded near3 (layer film) and (pnp npn)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 10:03
S1	0	triode adj (light-emitting or led).ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 07:49
S2	2	triode adj (light-emitting or led).ti, ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/01 17:48
S3	11	triode near4 (light-emitting or led).ti,ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/01 17:51
S4	0	triode near4 (light-emitting or led).ti,ab,clm. and graded near4 (layer or film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/01 17:50
S5	290	(257/101).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/01 17:51
S6	15	((257/101).CCLS.) and (high-frequency or GHz or gigahertz)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/01 18:02

S7	7	((257/101).CCLS.) and (high-frequency or GHz or gigahertz) and (graded or transition\$2) near12 (layer or film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/01 18:14
S8	4	((257/101).CCLS.) and graded near4 (layer or film) near12 offset near12 band	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/01 18:21
S9	9	"257"/\$6.ccls. and graded near4 (layer or film) near12 offset near12 band	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/01 18:25
S10	361	257/101	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/01 18:25
S11	9	257/101 and offset and (graded or transition\$2) near12 (layer or film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/01 18:33
S12	2	(257/101 or 372/43.ccls.) and (graded or transition\$2) near12 (layer or film) near12 active near12 base	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/01 18:35
S13	0	("(pnadjjunctionorp-nadjjunctionor pn-junction)near12offsetnear12graded").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/01 20:52
S14	0	(pn adj junction or p-n adj junction or pn-junction) near12 offset near12 graded	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/01 20:52
S15	140	(pn adj junction or p-n adj junction or pn-junction) near12 offset	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/01 20:52
S16	0	(pn adj junction or p-n adj junction or pn-junction) near15 offset near15 graded	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/01 20:53

S17	188	(pn adj junction or p-n adj junction or pn-junction) near15 graded	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/01 20:58
S18	33	(pn adj junction or p-n adj junction or pn-junction) near10 (graded near3 (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/01 20:54
S19	1	(pn adj junction or p-n adj junction or pn-junction) near10 (graded near3 (layer or film)) near10 band	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/01 20:56
S20	3	("4032951").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/01 20:56
S21	7	(pn adj junction or p-n adj junction or pn-junction) near15 graded and (257/101.ccls. or 372/43.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/01 21:07
S22	19	active adj (layer or film) near15 graded and (257/101.ccls. or 372/43.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/01 21:42
S23	2	jp-60202981\$-\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/01 21:42
S24	18378	((257/79) or (257/80) or (257/81) or (257/82) or (257/83) or (257/84) or (257/85) or (257/86) or (257/87) or (257/88) or (257/89) or (257/90) or (257/91) or (257/92) or (257/93) or (257/94) or (257/95) or (257/96) or (257/97) or (257/98) or (257/99) or (257/100) or (257/101) or (257/102) or (257/103) or (372/43) or (372/44) or (372/45) or (372/46) or (372/47) or (372/48) or (372/49) or (372/50)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/02 13:51

S25	11	((257/79) or (257/80) or (257/81) or (257/82) or (257/83) or (257/84) or (257/85) or (257/86) or (257/87) or (257/88) or (257/89) or (257/90) or (257/91) or (257/92) or (257/93) or (257/94) or (257/95) or (257/96) or (257/97) or (257/98) or (257/99) or (257/100) or (257/101) or (257/102) or (257/103) or (372/43) or (372/44) or (372/45) or (372/46) or (372/47) or (372/48) or (372/49) or (372/50)).CCLS.) and active adj (layer or film) near12 (graded near2 composition or graded-composition)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/02 10:44
S26	2	jp-04120786\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/02 10:30
S27	4	("5476811").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/02 13:26
S28	20	(US-5476811-\$ or US-5159603-\$ or US-5642372-\$ or US-6350997-\$ or US-5311539-\$ or US-5329134-\$ or US-5610413-\$ or US-5548137-\$ or US-5633527-\$ or US-6072189-\$ or US-4032951-\$ or US-5670798-\$).did. or (US-20020030195-\$).did. or (JP-04120786-\$ or JP-60202981-\$).did. or (US-5476811-\$ or JP-60202981-\$ or US-4032951-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2002/09/02 13:09
S29	13	((US-5476811-\$ or US-5159603-\$ or US-5642372-\$ or US-6350997-\$ or US-5311539-\$ or US-5329134-\$ or US-5610413-\$ or US-5548137-\$ or US-5633527-\$ or US-6072189-\$ or US-4032951-\$ or US-5670798-\$).did. or (US-20020030195-\$).did. or (JP-04120786-\$ or JP-60202981-\$).did. or (US-5476811-\$ or JP-60202981-\$ or US-4032951-\$).did.) and (step or stepwise)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/02 10:52

S30	1	257/101.ccls. and (graded or graded-composition) adj2 active adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/02 10:53
S31	2	("5159603").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/02 13:09
S32	2	("6350997").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/02 13:10
S33	290	(257/101).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/02 13:39
S34	0	(257/101andgradednear6active).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/02 13:39
S35	5	257/101 and graded near6 active	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/02 13:40
S36	0	("gradednear12activeand(light-emittingorlightadjemitting).ti,ab,clm.").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/03/02 13:10
S37	90	graded near12 active and (light-emitting or light adj emitting).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/02 13:44
S38	5	graded near12 active near12 (match\$3 or lattice-match\$3) and (light-emitting or light adj emitting).ti,ab,clm. and GaAs	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/02 15:24



S39	2	("6072189").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/03/02 15:24
S40	4	("5476811").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/03/02 15:32
S41	0	step-wise near3 graded near6 (match\$3 or lattice-match\$3) and (light-emitting or light adj emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/02 15:33
S42	2	step-wise near3 graded and (light-emitting or light adj emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/02 15:34
S43	2	step-wise near3 graded adj layer and (light-emitting or light adj emitting or laser)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/02 15:36
S44	16	step near3 graded adj layer and (light-emitting or light adj emitting or laser)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/02 15:37
S45	10	step near3 graded adj layer and (light-emitting or light adj emitting or laser).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/02 15:39
S46	3	step-graded adj layer and (light-emitting or light adj emitting or laser).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/02 15:41
S47	7	step-graded near3 layer and (light-emitting or light adj emitting or laser).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/02 15:53
S48	4	"895213".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/02 15:56



S49	13	step-wise near3 (layer or multi-graded or multi-layer) and (light-emitting or light adj emitting or laser).ti,ab,clm. and (match\$3 or lattice-match\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/02 15:58
S50	2	jp-04075347\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/28 14:08
S51	2	jp-61059793\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/28 14:04
S52	2	jp-02280338\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/28 14:04
S53	2	jp-03008340\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/28 14:11
S54	2	jp-61053768\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/28 14:13
S55	2	jp-61131491\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/28 14:15
S56	2	("5010382").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/06/28 15:44
S57	3	graded near12 (lattice-match\$3 lattice near2 match\$3) and active adj (layer region) and (light-emitting light adj emitting semiconductor adj laser laser adj diode) and base and emitter and collector	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/28 16:48

S58	2	("5010382").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/06/28 16:45
S59	9	(graded lattice-match\$3 lattice near2 match\$3) near15 active adj (layer region) and (light-emitting light adj emitting semiconductor adj laser laser adj diode) and base and emitter and collector	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/28 17:04
S60	0	graded near12 (lattice-match\$3 lattice near2 match\$3) near15 active adj (layer region) and (light-emitting light adj emitting semiconductor adj laser laser adj diode led) and base and emitter and collector	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/28 17:06
S61	5	(lattice-match\$3 lattice near2 match\$3) near15 active and (light-emitting light adj emitting semiconductor adj laser laser adj diode led) and base and emitter and collector	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/28 17:07
S62	47	(hbt heterojunction adj bipolar adj transistor).ti,ab,clm. and (light adj emitting light-emitting).ti,ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/29 09:32
S63	5	(hbt heterojunction adj bipolar adj transistor).ti,ab,clm. and (light adj emitting light-emitting).ti,ab. and (graded grading grinsch)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/29 09:52
S64	2	("5010382").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/06/29 09:52
S65	0	((("5010382").PN.) and base and active and (graded graded adj composition) and (light adj emitting light-emitting light laser)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/29 10:27
S66	0	((("5010382").PN.) and base and active and (graded graded adj composition)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/29 09:54

S67	0	((("5010382").PN.) and base and active and (stepped step-wise stepwise graded graded adj composition)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/29 09:55
S68	0	((("5010382").PN.) and base and active and (smooth smoothly varying transition stepped step-wise stepwise graded graded adj composition)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/29 09:56
S69	1	((("5010382").PN.) and base and (smooth smoothly varying transition stepped step-wise stepwise graded graded adj composition)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/29 10:27
S70	2	("5796714").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/06/29 10:27
S71	1	((("5796714").PN.) and base and (smooth smoothly varying transition stepped step-wise stepwise graded graded adj composition grading) and active	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/29 12:25
S72	320	(257/101).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/06/29 12:34
S73	0	("grinschandlight-emitting.ti,ab.").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/06/29 12:34
S74	2	grinsch and light-emitting.ti,ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/29 13:14
S75	0	"motorola" and lattice-match\$3 and grad\$3 near12 composition	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/29 13:15

S76	0	"motorola" and grad\$3 near12 base near12 (hbt or heterojunction adj bipolar adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/29 13:16
S77	13	yoshii.in. and shigeo.in. and ("257"/\$6.ccls. or "372"/\$6.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/30 07:09
S78	14866	372/4\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/30 07:16
S79	229	372/4\$1 and graded near12 active	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/30 07:13
S80	19	372/4\$1 and graded near12 active and recombination and speed	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/30 07:15
S81	2750	(372/46).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/06/30 07:19
S82	320	(257/101).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/06/30 07:16
S83	520	((372/46).CCLS.) and (graded grading lattice-match\$3 lattice adj match\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/30 07:22
S84	139	((372/46).CCLS.) and (graded grading lattice-match\$3 lattice adj match\$3).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/30 07:23
S85	70	((372/46).CCLS.) and (graded grading lattice-match\$3 lattice adj match\$3).ti,ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/30 07:29

S86	37	((372/46).CCLS.) and (graded grading lattice-match\$3 lattice adj match\$3).ti,ab. and gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/30 07:45
S87	4	("5476811").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/06/30 07:46
S88	2	("6072189").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/06/30 07:46
S89	0	(triode.ti,ab,clm.and(257/79.ccls. 257/8\$1.ccls.257/9\$1.ccls. 257/100.ccls.257/101.ccls. 257/102.ccls.257/103.ccls.)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/09/24 14:42
S90	9	triode.ti,ab,clm. and (257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/100.ccls. 257/101.ccls. 257/102.ccls. 257/103.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/09/24 14:44
S91	1	current adj control near12 triode and light-emitting adj2 device	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/09/24 14:47
S92	9	extinction adj ratio and 257/10?. ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/09/24 15:18
S93	8286	((257/79) or (257/80) or (257/81) or (257/82) or (257/83) or (257/84) or (257/85) or (257/86) or (257/87) or (257/88) or (257/89) or (257/90) or (257/91) or (257/92) or (257/93) or (257/94) or (257/95) or (257/96) or (257/97) or (257/98) or (257/99) or (257/100) or (257/101) or (257/102) or (257/103)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/09/24 15:20

S94	36	((257/79) or (257/80) or (257/81) or (257/82) or (257/83) or (257/84) or (257/85) or (257/86) or (257/87) or (257/88) or (257/89) or (257/90) or (257/91) or (257/92) or (257/93) or (257/94) or (257/95) or (257/96) or (257/97) or (257/98) or (257/99) or (257/100) or (257/101) or (257/102) or (257/103)).CCLS.) and graded and emitter and base and collector	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/04 10:00
S95	6	"895213".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/26 17:16
S96	2	light adj emission adj control.ti,ab, clm. and constant adj current adj control.ti,ab,clm. and light adj emitting adj (element device diode).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/26 17:17
S97	2	light adj emission adj control.ti,ab, clm. and constant adj current adj control.ti,ab,clm. and light adj emitting adj (element device diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/26 17:17
S98	2	light adj emission adj control.ti,ab, clm. and constant adj current adj control.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/26 17:17
S99	3	light adj emission adj control and constant adj current adj control.ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/26 17:23
S10 0	3	light adj emission adj control.ti,ab, clm. and constant adj current adj control	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/26 17:26
S10 1	0	light adj emission adj control adj circuit and constant adj current adj control adj circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/26 17:26
S10 2	2	light adj emission adj control adj circuit and current adj control adj circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/26 17:27

S10 3	10	light adj emission adj control near6 circuit and current adj control near6 circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/26 17:27
S10 4	2	"949634".AP.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/26 18:03
S10 5	10	mondtxa. and graded	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 14:08
S10 6	0	("895213.ap.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 14:09
S10 7	6	"895213".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 15:39
S10 8	2	("5010382").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:35
S10 9	6567	((257/79) or (257/8\$1) or (257/9\$1) or (257/100) or (257/101) or (257/102) or (257/103)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/05/03 16:36
S11 0	454	S109 and graded	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:37
S11 1	28	S109 and graded and control\$4 near6 emission	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:51
S11 2	0	(PNP NPN) near6 graded and S109	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:52



S11 3	0	(PNP NPN) near3 diode and S109 and graded	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:52
S11 4	1	(PNP NPN) near3 diode and S109 and (lattice adj matching buffer graded)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:54
S11 5	1	(PNP NPN n-p-n p-n-p) near3 diode and S109 and (lattice adj matching buffer graded)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:54
S11 6	0	(PNP NPN n-p-n p-n-p) near3 S109 and (lattice adj matching buffer graded)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:54
S11 7	84	(PNP NPN n-p-n p-n-p) and S109 and (lattice adj matching buffer graded)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:58
S11 8	50	(PNP NPN n-p-n p-n-p) and S109 and (lattice adj matching graded)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 16:58